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Renesas Electronics website: http://www.renesas.com

April 1st, 2010 Renesas Electronics Corporation

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R1LV1616RBA-5SI

16Mb Advanced LPSRAM (1M wordx16bit / 2M wordx8bit)

Description

The R1LV1616R Series is a family of low voltage 16-Mbit static RAMs organized as 1048576-words by 16-bit, fabricated by Renesas's high-performance 0.15um CMOS and TFT technologies.

The R1LV1616R Series is suitable for memory applications where a simple interfacing , battery operating and battery backup are the important design objectives.

The R1LV1616RBA Series is packaged in a 48balls Wafer Level Chip Scale Package[WL-CSP / 5.62mm x 5.84mm with the ball-pitch of 0.55mm and the height of 0.79mm]. It gives the best solution for a compaction of mounting area as well as flexibility of wiring pattern of printed circuit boards.

Features

- Single 2.7-3.6V power supply
- Small stand-by current:2µA (3.0V, typ.)
- Data retention supply voltage =2.0V
- No clocks, No refresh
- All inputs and outputs are TTL compatible
- Easy memory expansion by CS1#, CS2, LB# and UB#
- Common Data I/O
- Three-state outputs: OR-tie capability
- OE# prevents data contention on the I/O bus
- Process technology: 0.15um CMOS

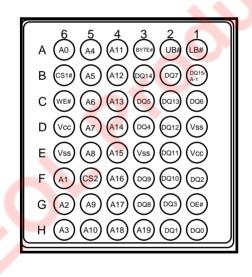


Ordering Information

Type No.	Access time	Package
R1LV1616RBA-5SI	55 ns	5.62mmx5.84mm WL-CSP with 0.55mm pitch 48balls

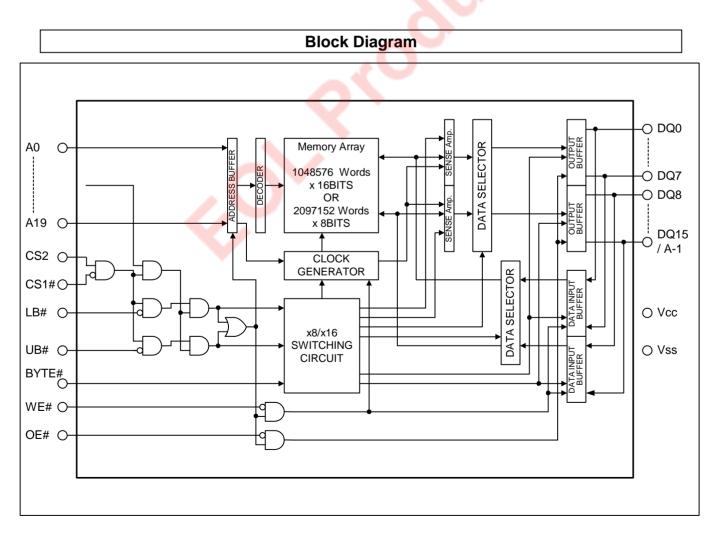
Pin Arrangement

48-pin WL-CSP (bottom view)





Pin Description						
Pin name	Function					
A0 to A19	Address input					
DQ 0 to DQ15	Data input/output					
CS1# &CS2	Chip select					
WE#	Write enable					
OE#	Output enable					
LB#	Lower byte select					
UB#	Upper byte select					
Vcc	Power supply					
Vss	Ground					
BYTE#	Byte (x8 mode) enable input					
NC	Non connection					



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	Operating Table										
CS1#	CS2	BYTE#	LB#	UB#	WE#	OE#	DQ0-7	DQ8-14	DQ15	Operation	
н	Х	Х	Х	Х	Х	Х	High-Z	High-Z	High-Z	Stand by	
Х	L	Х	Х	Х	Х	Х	High-Z	High-Z	High-Z	Stand by	
Х	Х	Н	Н	Н	Х	Х	High-Z	High-Z	High-Z	Stand by	
L	Н	Н	L	Н	L	Х	Din	High-Z	High-Z	Write in lower byte	
L	Н	Н	L	Н	Н	L	Dout	High-Z	High-Z	Read from lower byte	
L	Н	Х	Х	Х	Н	Н	High-Z	High-Z	High-Z	Output disable	
L	Н	Н	Н	L	L	Х	High-Z	Din	Din	Write in upper byte	
L	Н	Н	Н	L	Н	L	High-Z	Dout	Dout	Read from upper byte	
L	Н	Н	L	L	L	Х	Din	Din	Din	Write	
L	Н	Н	L	L	Н	L	Dout	Dout	Dout	Read	
L	Н	L	L	L	L	Х	Din	High-Z	A-1	Write	
L	Н	L	L	L	Н	L	Dout	High-Z	A-1	Read	

Note 1. H:VIH L:VIL X: VIH or VIL

2. When applying BYTE# ="L", please assign LB#=UB#="L".

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Power supply voltage relative to Vss	Vcc	-0.5 to +4.6	V
Terminal voltage on any pin relation toVss	Vт	-0.5*1 to Vcc+0.3*2	V
Power dissipation	Рт	0.7	W
Operation temperature	Topr	-40 to +85	٥C
Storage temperature	Tstg	-65 to +150	٥C
Storage temperature range under bias	Tbias	-40 to +85	٥C

Note 1. -2.0V in case of AC (Pulse width \leq 30ns)

2. Maximum voltage is +4.6V



Parameter	Symbol	Min.	Тур.	Max.	Unit	Note
Supply voltage	Vcc	2.7	3.0	3.6	V	
Supply voltage	Vss	0	0	0	V	
Input high voltage	Vін	2.4	-	Vcc+0.2	V	
Input low voltage	VIL	-0.2	-	0.4	V	1
Ambient temperature range	Та	-40	-	+85	٥C	2

Recommended Operating Conditions

Note 1. –2.0V in case of AC (Pulse width \leq 30ns)

DC Characteristics

Parameter	Symbol	Min.	Typ.*1	Max.	Unit	Test conditions ^{*2}		
Input leakage current	I LI	-	-	1	μA	Vin=Vss to Vcc		
Output leakage current	ILo	-		1	μA	CS1# =VIH or CS2=VIL or OE# = VIH or WE# =VIL or LB# =UB# =VIH,VI/O=Vss to Vcc		
Average operating	Icc1	-	25	40	mA	Min. cycle, duty =100% I I/O = 0 mA, CS1# =VIL, CS2=VIH Others = VIH / VIL		
Average operating current	ICC2		2	5	mA	$\begin{array}{l} Cycle \ time = 1 \ \mu s, \ I \ {\it I/O} = 0 \ mA, \\ CS1\# \le 0.2V, \ CS2 \ge Vcc\text{-}0.2V \\ V\text{IH} \ge Vcc\text{-}0.2V \ , \ V\text{IL} \le 0.2V, \\ duty = 100\% \end{array}$		
Standby current	Isb	-	0.1	0.3	mA	CS2=VIL		
		-	2	6	μA	~+25⁰C V in ≥ 0V (1) 0V≤CS2≤0.2V or		
Standby ourrant		-	4	12	μA	~+40°C (2) CS2≥Vcc-0.2V, CS1# ≥Vcc-0.2V or		
Standby current	ISB1	-	-	25	μA	~+70°C (3)LB# =UB# ≥Vcc-0.2V, CS2≥Vcc-0.2V,		
		-	-	40	μA	CS1# ≤0.2V ∼+85⁰C Average value		
Output hige voltage	Vон	2.4	-	-	V	Іон = -1mA		
Output Low voltage	Vol	-	-	0.4	V	IOL = 2mA		

Note 1. Typical parameter indicates the value for the center of distribution at 3.0V (Ta= $25^{\circ}C$), and not 100% tested. 2. BYTE# \geq Vcc-0.2V or BYTE# \leq 0.2V

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Capacitance

(Ta = +25°C, f =1MHz)

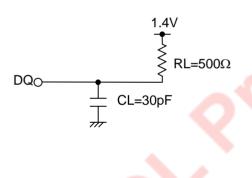
Parameter	Symbol	Min.	Тур.	Max.	Unit	Test conditions	Note
Input capacitance	C in	-	-	10	pF	V in = 0V	1
Input / output capacitance	С і/о	-	-	10	pF	V I/O = 0V	1

Note 1:This parameter is sampled and not 100% tested.

AC Characteristics

Test Conditions (Vcc=2.7~3.6V, Ta = -40~+85°C *)

- Input pulse levels: VIL= 0.4V,VIH=2.4V
- Input rise and fall time : 5ns
- Input and output timing reference levels : 1.4V
- Output load : See figures (Including scope and jig)





Read Cycle

Deresseter	Ourseland	(no	te0)	L les it	Natas				
Parameter	Symbol	Min.	Max.	Unit	Notes				
Read cycle time	t RC	55	-	ns					
Address access time	t AA	-	70	ns					
Chip select access time	t ACS1	-	55	ns					
Chip select access time	t _{ACS2}	-	55	ns					
Output enable to output valid	t oe	-	35	ns					
Output hold from address change	tон	10	-	ns					
LB#,UB# access time	tва	-	55	ns					
Chip select to output in low-Z	t clz	10	-	ns	2,3				
LB#,UB# enable to low-Z	t BLZ	5	-	ns	2,3				
Output enable to output in low-Z	t olz	5	C	ns	2,3				
Chip deselect to output in high-Z	tcHz1	0	20	ns	1,2,3				
Chip deselect to output in high-2	t снz2	0	20	ns	1,2,3				
LB#,UB# disable to high-Z	t внz	0	20	ns	1,2,3				
Output disable to output in high-Z	tонz	0	20	ns	1,2,3				



Write Cycle

Parameter	Symbol	Vcc=2.7	V to 3.6V	Unit	Notes	
	Symbol	Min.	Max.	Unit	10103	
Write cycle time	t wc	55	-	ns		
Address valid to end of write	taw	50	-	ns		
Chip selection to end of write	t cw	55	-	ns	5	
Write pulse width	twp	40	-	ns	4	
LB#,UB# valid to end of write	tвw	50	-	ns		
Address setup time	t AS	0	-	ns	6	
Write recovery time	t wr	0	-	ns	7	
Data to write time overlap	t ow	25	-	ns		
Data hold from write time	tон	0	-	ns		
Output active from end of write	tow	5	-	ns	2	
Output disable to output in high-Z	tонz	0	20	ns	1,2	
Write to output in high-Z	twнz	0	20	ns	1,2	

- Note0. 55ns parts can be supported under the condition of the input timing limitation toward SRAM on customer's system. Please contact our sales office in your region, in case of the inquiry for 55ns parts. In case of tAA =70ns, tRc =70ns.
 - 1. tCHZ, tOHZ, tWHZ and tBHZ are defined as the time at which the outputs achieve the open circuit conditions and are not referred to output voltage levels.
 - 2. This parameter is sampled and not 100% tested.
 - 3. AT any given temperature and voltage condition, tHz max is less than tLz min both for a given device and form device to device.
 - 4. A write occurs during the overlap of a low CS1#, a high CS2, a low WE# and a low LB# or a low UB#. A write begins at the latest transition among CS1# going low, CS2 going high, WE# going low and LB# going low or UB# going low .

A write ends at the earliest transition among CS1# going high, CS2 going low, WE# going high and LB# going high or UB# going high. twp is measured from the beginning of write to the end of write.

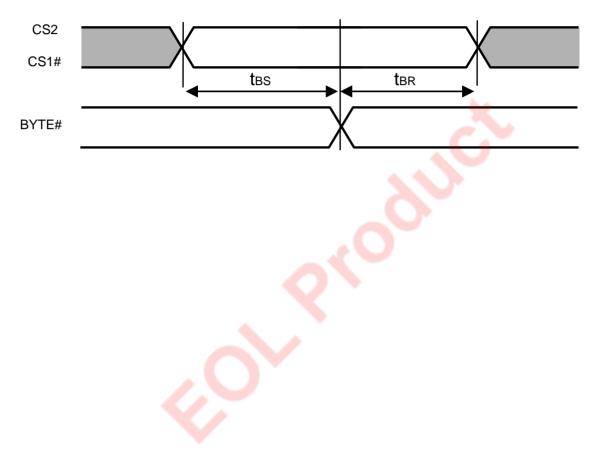
- 5. tcw is measured from the later of CS1# going low or CS2 going high to end of write.
- 6. tAs is measured the address valid to the beginning of write.
- 7. twR is measured from the earliest of CS1# or WE# going high or CS2 going low to the end of write cycle.



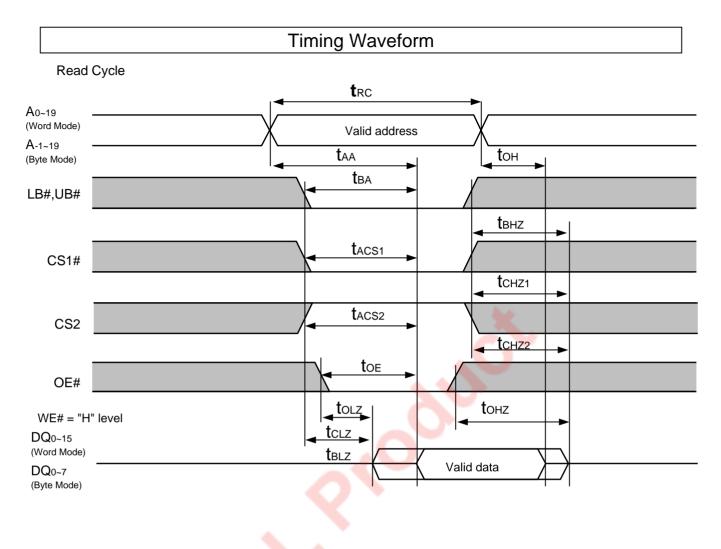
Timing condition for Byte enable

Parameter	Symbol	Min.	Max.	Unit	Notes
Byte setup time	t вs	5	-	ms	
Byte recovery time	t BR	5	-	ms	

BYTE# Timing Waveform



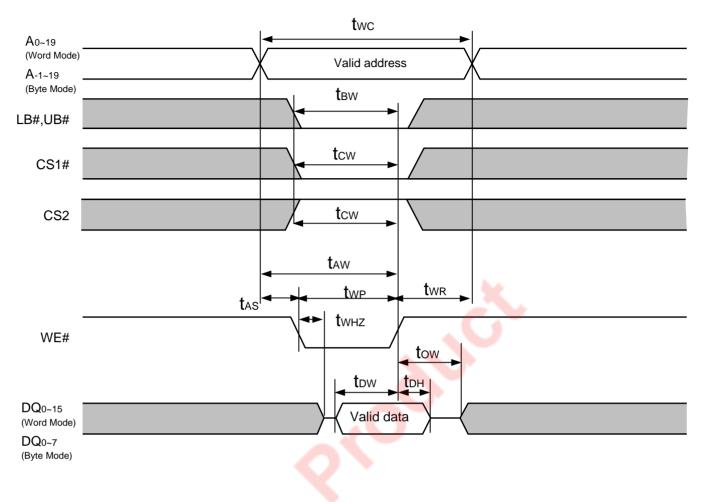




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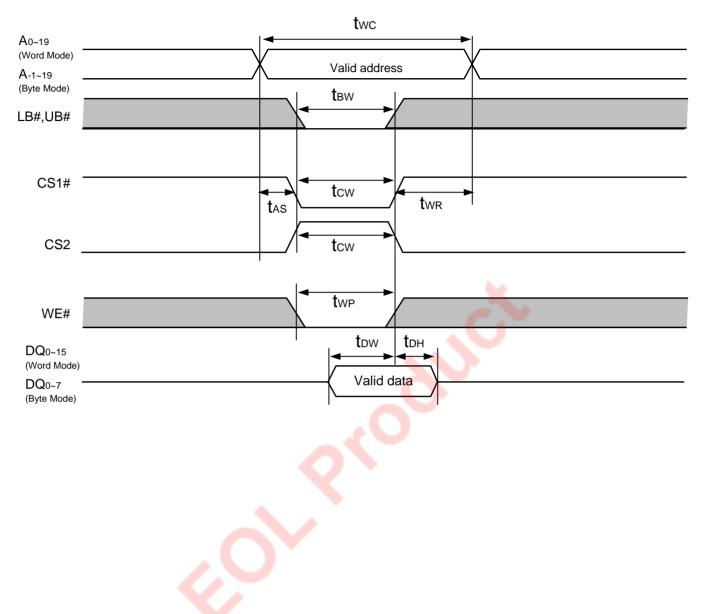
Write Cycle (1) (WE# Clock)



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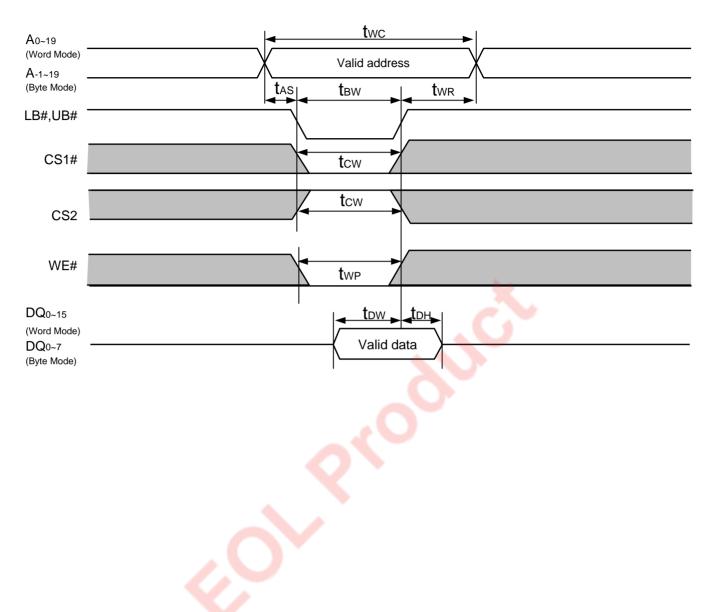


Write Cycle (2) (CS1# ,CS2 Clock, OE#=VIH)





Write Cycle (3) (LB#,UB# Clock, OE#=VIH)





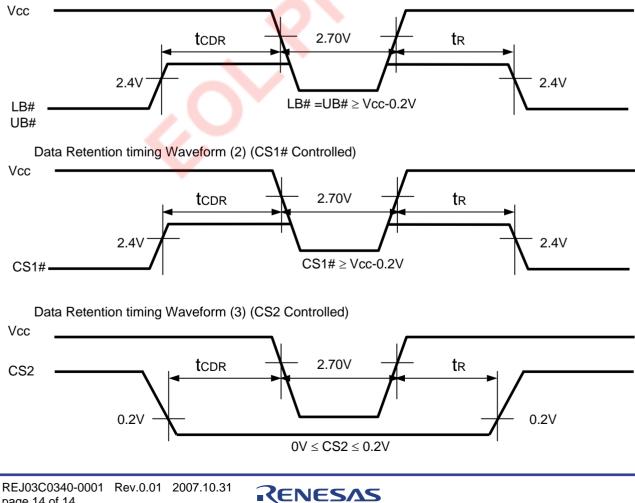
Data Retention Characteristics								
Parameter	Symbol	Mln.	Typ.*1	Max.	Unit	Test conditions*2,3		
Vcc for data retention	Vdr	2.0	-	3.6	V	$ \begin{array}{l} V \text{ in } \geq 0V \\ (1) \ 0V \leq CS2 \leq 0.2V \ \text{or} \\ (2) \ CS2 \geq Vcc\text{-}0.2V, \\ CS1\# \geq Vcc\text{-}0.2V \ \text{or} \\ (3) \ LB\# = UB\# \geq Vcc\text{-}0.2V, \\ CS2 \geq Vcc\text{-}0.2V, \\ CS1\# \leq 0.2V \end{array} $		
	ICCDR	-	2	6	μA	~+25°C	Vcc=3.0V,Vin \ge 0V (1) 0V \le CS2 \le 0.2V or	
Data retention current		-	4	12	μA	~+40°C	(1) $0V \le CS2 \le 0.2V$ of (2) $CS2 \ge Vcc-0.2V$, $CS1\# \ge Vcc-0.2V$ or	
		-	-	25	μA	~+70°C	(3) LB# =UB# ≥Vcc-0.2V, CS2 ≥ Vcc-0.2V, CS1# < 0.2V	
		-	-	40	μA	~+85°C	Average value	
Chip deselect to data retention time	t CDR	0	-	-	ns	See retention waveform		
Operation recovery time	tR	5	-	-	ms			

Note 1. Typical parameter of ICCDR indicates the value for the center of distribution at Vcc=3.0V and not 100% tested.

2. BYTE# pin supported only by TSOP and uTSOP types. BYTE# \geq Vcc-0.2V or BYTE# \leq 0.2V

3. Also CS2 controls address buffer, WE# buffer ,CS1# buffer ,OE# buffer ,LB# ,UB# buffer and Din buffer .If CS2 controls data retention mode, Vin levels (address, WE#, OE#, CS1#, LB#, UB#, I/O) can be in the high impedance state. If CS1# controls data retention mode, CS2 must be $CS2 \ge Vcc-0.2V$ or $0V \le CS2 \le 0.2V$. The other input levels (address, WE#, OE#, CS1#, LB#, UB#, I/O) can be in the high impedance state.

Data Retention timing Waveform (1) (LB#,UB# Controlled)



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